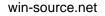


THE DATASHEET OF DSS5240Y-7





0086-755-83957316



DSS5240Y 40V LOW V_{CE(sat)} PNP SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- Ultra Small Surface Mount Package
- "Lead Free", RoHS Compliant (Note 1)
- Halogen and Antimony Free, "Green Device" (Note 2)
- ESD rating: 400V-MM, 8KV-HBM

Mechanical Data

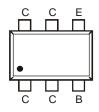
- Case: SOT-363
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper Plated Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (approximate)



Top View



Device Symbol



Top View Pin Out Configuration

Ordering Information (Note 3)

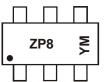
Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DSS5240Y-7	ZP8	7	8mm	3,000

1. No purposefully added lead.

2. Diodes Inc's "Green" Policy can be found on our website at http://www.diodes.com

3. For packaging details, go to our website at http://www.diodes.com

Marking Information



ZP8 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: W = 2009) M = Month (ex: 9 = September)

Date Code Key

Notes:

Year	2009		2010	2011		2012	2013		2014	2015		2016
Code	W		Х	Y		Z	А		В	С		D
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



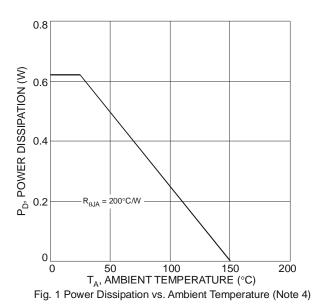
Maximum Ratings $@T_A = 25^{\circ}C$ unless otherwise specified

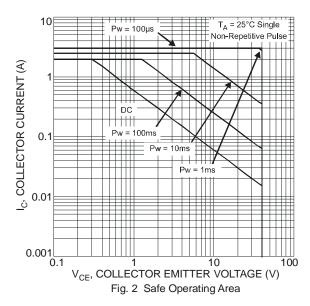
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current - Continuous	lc	-2	A
Peak Pulse Collector Current	I _{CM}	-3	A
Base Current (DC)	IB	-300	mA
Peak Base Current	I _{BM}	-1	A

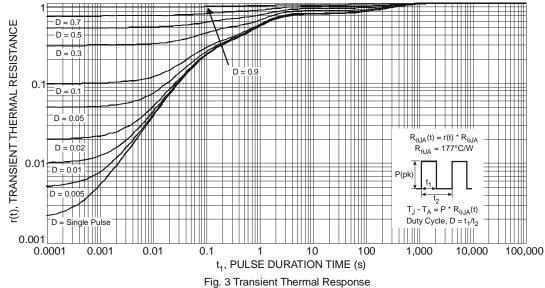
Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4) @ $T_A = 25^{\circ}C$	PD	625	mW
Thermal Resistance, Junction to Ambient (Note 4) @ $T_A = 25^{\circ}C$	$R_{ heta JA}$	200	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	۵°

Notes: 4. Device mounted on FR-4 PCB, with minimum recommended pad layout.





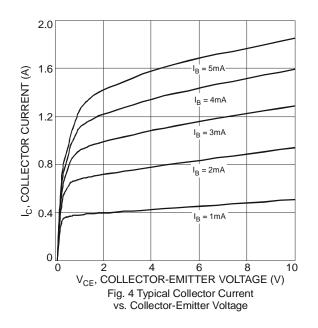


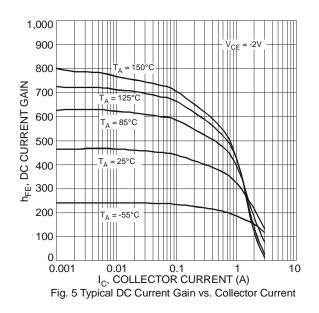


Electrical Characteristics @T_A = 25°C unless otherwise specified

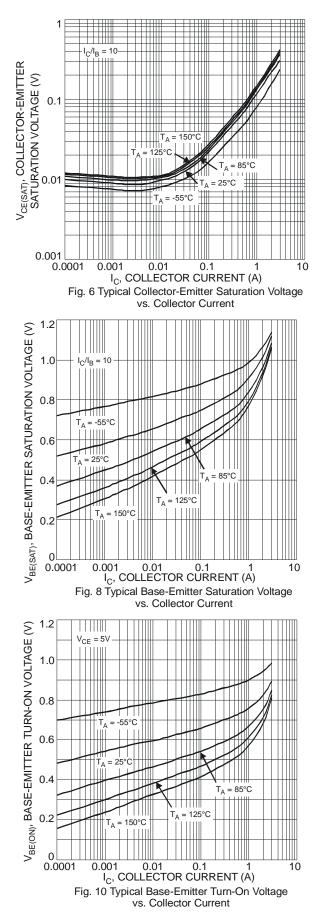
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-40			V	$I_{\rm C} = -100 \mu A, I_{\rm E} = 0$
Collector-Emitter Breakdown Voltage (Note 5)	BVCBO	-40			V	$I_{\rm C} = -10 \text{mA}, I_{\rm B} = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	-5			V	$I_{\rm E} = -100 \mu A, I_{\rm C} = 0$
Collector Cutoff Current	ICBO	_	_	-100	nA	$V_{CB} = -30V, I_E = 0$
				-50	μA	V _{CB} = -30V, I _E = 0, T _A = 150°C
Emitter Cutoff Current	I _{EBO}	—	—	-100	nA	$V_{EB} = -4V, I_{C} = 0$
		300	450	_		$V_{CE} = -2V, I_{C} = -100mA$
DC Current Gain (Note 5)	hFE	260	380	—		$V_{CE} = -2V, I_C = -500mA$
		210	325	—		$V_{CE} = -2V, I_{C} = -1A$
		100	210	—		$V_{CE} = -2V, I_{C} = -2A$
			—	-100		$I_{C} = -100 \text{mA}, I_{B} = -1 \text{mA}$
				-110	mV	$I_{C} = -500 \text{mA}, I_{B} = -50 \text{mA}$
Collector-Emitter Saturation Voltage (Note 5)	V _{CE(sat)}	_	—	-225		I _C = -750mA, I _B = -15mA
				-225		I _C = -1A, I _B = -50mA
		_	_	-350		I _C = -2A, I _B = -200mA
Collector-Emitter Saturation Resistance	R _{CE(sat)}	_	_	-220	mΩ	I _C = -500mA, I _B = -50mA
Base-Emitter Saturation Voltage (Note 5)	V _{BE(sat)}	_	-1.0	-1.1	V	$I_{C} = -2A, I_{B} = -200 \text{mA}$
Base-Emitter Turn On Voltage (Note 5)	V _{BE(on)}		-0.67	-0.75	V	$V_{CE} = -2V, I_{C} = -100mA$
Output Capacitance	C _{obo}	_	25	40	pF	V _{CB} = -10V, f = 1.0MHz
Current Gain-Bandwidth Product	f _T	100	220	_	MHz	$V_{CE} = -10V, I_{C} = -50mA, f = 100MHz$
Turn-On Time	t _{on}	_	73		ns	
Delay Time	t _d	_	27	_	ns	
Rise Time	tr		46	_	ns	$V_{CC} = -10V$
Turn-Off Time	t _{off}	_	237	_	ns	$I_{C} = -1A$, $I_{B1} = I_{B2} = -50mA$
Storage Time	ts	_	195	_	ns	
Fall Time	t _f		42		ns	7

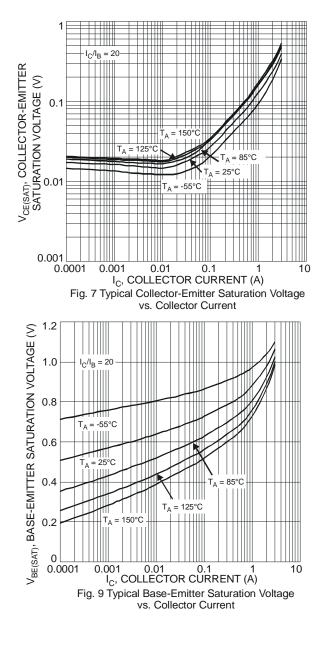
Notes: 5. Measured under pulsed conditions. Pulse width = $300\mu s$. Duty cycle $\leq 2\%$.





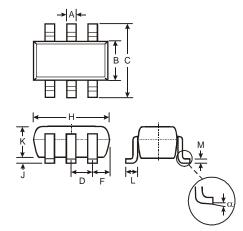






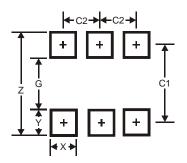


Package Outline Dimensions



	SOT-363						
Dim	Min Max						
Α	0.10	0.30					
В	1.15	1.35					
С	2.00	2.20					
D	0.65 Typ						
F	0.40	0.45					
Н	1.80 2.20						
J	0 0.10						
К	0.90 1.00						
L	0.25 0.40						
М	0.10	0.22					
α	0°	8°					
All Dimensions in mm							

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Y	0.6
C1	1.9
C2	0.65



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